

**Silicon PNP Power Transistors**

**2SA914**

**DESCRIPTION**

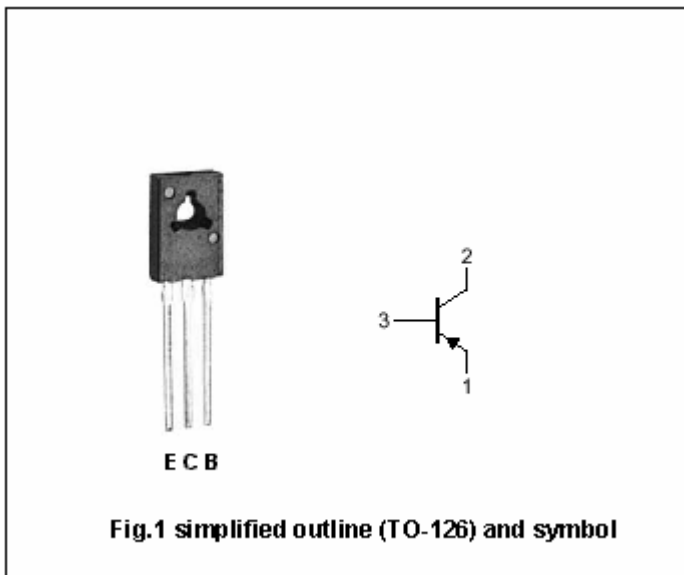
- With TO-126 package
- Complement to type 2SC1953
- Good linearity of  $h_{FE}$
- High  $V_{CEO}$

**APPLICATIONS**

- For audio frequency power pre-amplifier

**PINNING**

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



**Absolute Maximun Ratings (Ta=25°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-150	V
$V_{CEO}$	Collector-emitter voltage	Open base	-150	V
$V_{EBO}$	Emitter-base voltage	Open collector	-5	V
$I_C$	Collector current		-50	mA
$I_{CM}$	Collector current-Peak		-100	mA
$P_C$	Collector power dissipation		1	W
$T_j$	Junction temperature		150	°C
$T_{stg}$	Storage temperature		-55~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-0.1mA; I <sub>B</sub> =0	-150			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =-10μA; I <sub>C</sub> =0	-5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-30mA; I <sub>B</sub> =-3mA			-1.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-100V; I <sub>E</sub> =0			-1	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-5V; I <sub>C</sub> =0			-1	μA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =-10mA; V <sub>CE</sub> =-5V	90		450	
C <sub>OB</sub>	Output capacitance	I <sub>E</sub> =0; V <sub>CB</sub> =-10V; f=1MHz			5	pF
f <sub>T</sub>	Transition frequency	I <sub>E</sub> =10mA; V <sub>CB</sub> =-10V		200		MHz

◆ h<sub>FE</sub> Classifications

Q	R	S	T
90-155	130-220	185-330	260-450

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PACKAGE OUTLINE

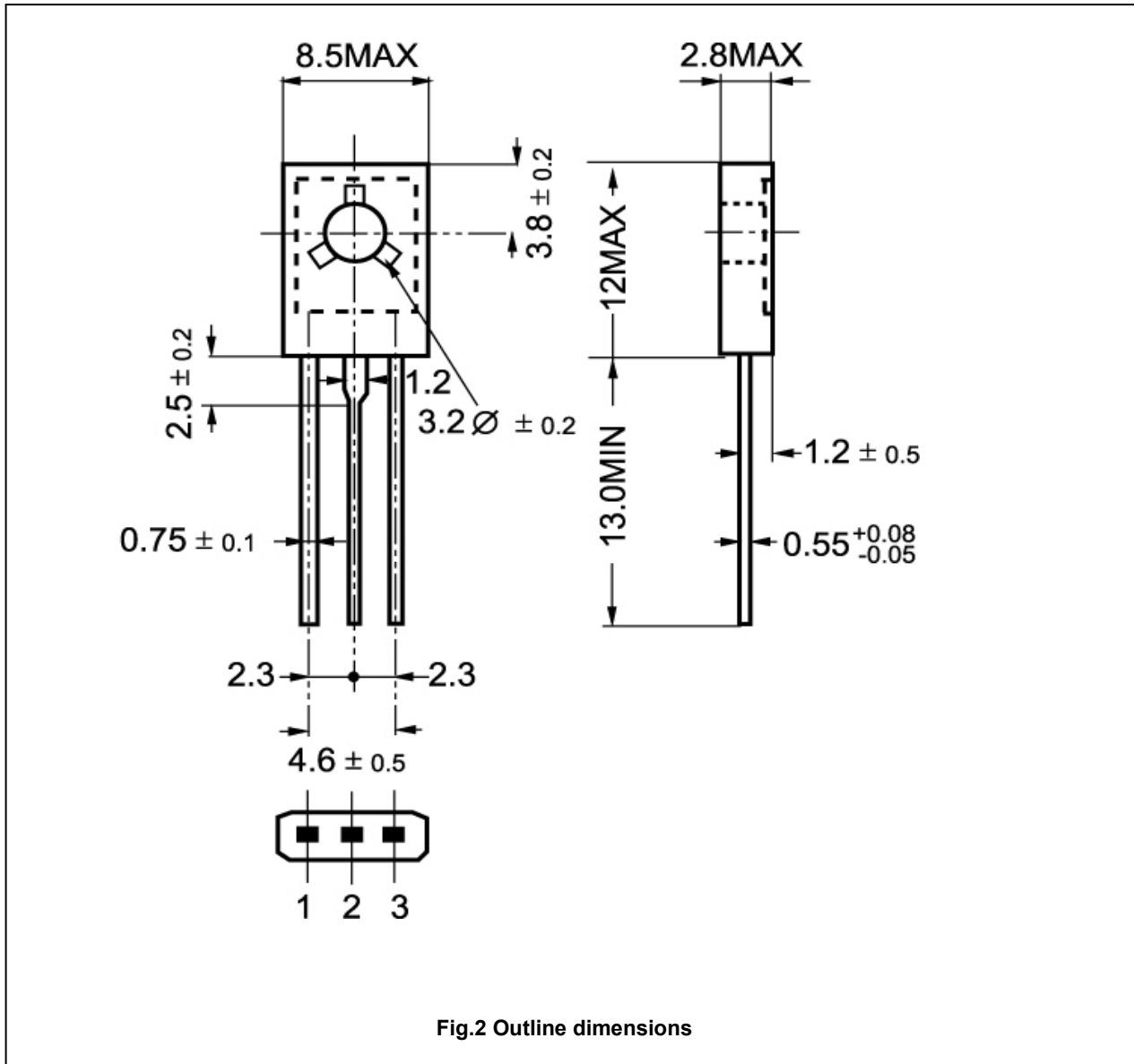


Fig.2 Outline dimensions